



TO-251-3L Plastic-Encapsulate Transistors

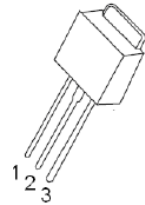
2SD1760 TRANSISTOR (NPN)

FEATURES

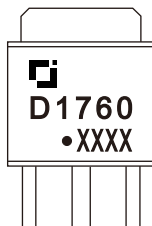
- Low $V_{CE(sat)}$
- Complements the 2SB1184

TO-251-3L

1. BASE
2. COLLECTOR
3. EMITTER

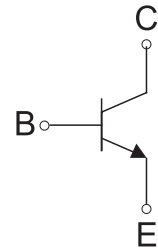


MARKING



D1760=Device code
Solid dot=Green moldinn compound device,
if none,the normal device
XXXX=Code

Equivalent Circuit



MAXIMUM RATINGS ($T_a=25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	3	A
P_C	Collector Power Dissipation	1.5	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55 to +150	$^{\circ}\text{C}$

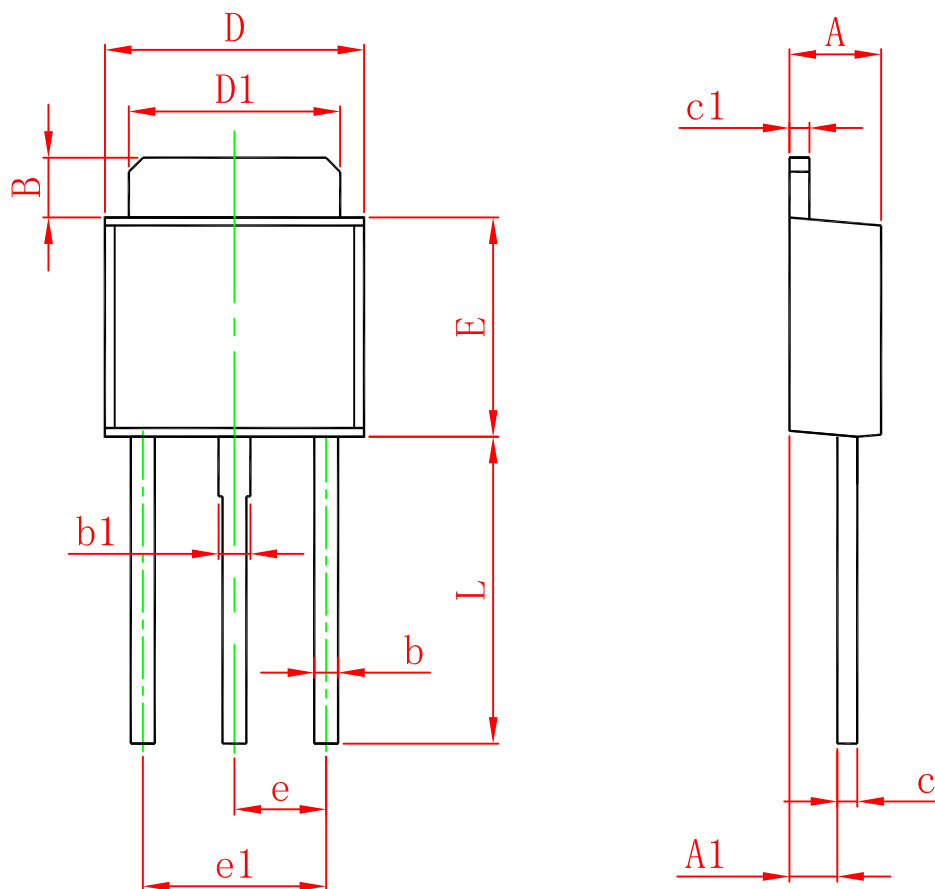
ELECTRICAL CHARACTERISTICS (T_a=25°C unless other wise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =40V, I _E =0			1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			1	μA
DC current gain	h _{FE}	V _{CE} =3V, I _C =500mA	82		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =2A, I _B =200mA			1	V
Transition frequency	f _T	V _{CE} =5V, I _C =500mA, f=30MHz		90		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		40		pF

CLASSIFICATION of h_{FE}

Rank	P	Q	R
Range	82-180	120-270	180-390

TO-251-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311